

# Advances in packaging interconnects IMAPS-UK Research Showcase 11th & 12th of January, 2021

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Prof Chris Bailey, Prof Hua Lu (University of Greenwich)

Sincere thanks to Oscar Khaselev and Mike Marczi of Cookson Electronics for providing Ag nanoparticle paste, and to Dr Kim Evans & Dr Mumby-Croft, Dynex Semiconductor Ltd. for the provision of Al and Cu wire bond samples

The work was supported by Mentor Graphics, the UK Engineering and Physical Sciences Research Council projects EP/K035304/1 & EP/R004366/1 through the Centre for Power Electronics, the Innovative Electronics Manufacturing Research Centre (IeMRC) EP/H03014X/1, the Engineering and Physical Sciences Partnered Access Fund (2017) and the EU Commission's 7th Framework Programme Cleansky2 JU EMINEO

# Overview of session



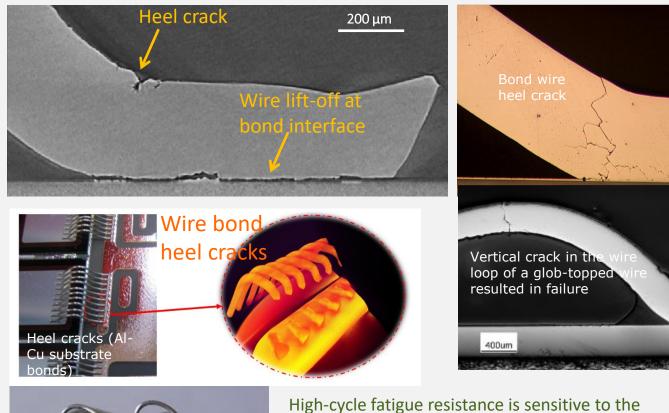
- Typical interconnect failures
- Overview of candidate interconnection technologies for higher operational temperatures
- Ultrasonic wire bond interconnects
  - Al, Cu, others...
- Die attach options
  - Pb-free solders, sintered nanoAg attach

# Interconnect failure mechanisms



#### Wire bond cracking under temperature cycling

Wire bond lift-offs

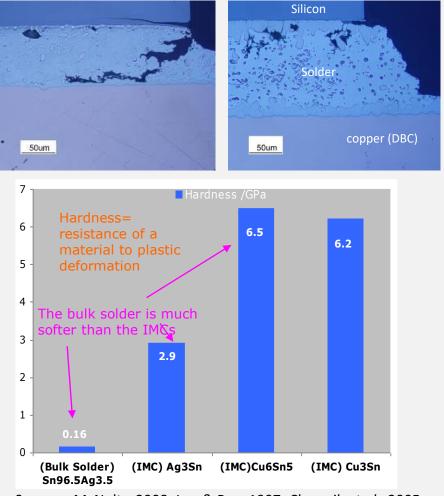


High-cycle fatigue resistance is sensitive to the nucleation of micro-cracks at microstructural inhomogeneities

# Microstructural changes within solder affect its bulk properties over time

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Sources: McNulty, 2008; Lau & Pao, 1997; Chomrik *et al.*, 2005; Chomrik *et al.*, 2003; Harris & Rubel, 2008.

# Candidate interconnect technologies for WBG



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#### Benefits, Challenges and Constraints

- High switching frequency, higher power densities, improved energy conversion efficiency
- Can exploit higher levels of package integration
- Higher power densities- higher packaging temperatures

Interconnections dominate failure process and ultimately determine package reliability

#### New attachment methods need to offer

- High temperature stability
- High performance in terms of thermal and electrical conductivity
- Manufacturing flexibility and compatibility with highly integrated designs and topologies
- High reliability and robustness (longevity under harsh/extreme operating environments)
- Sustainability (holistic appraisal & minimisation of environment, health, geopolitical impacts)

# Candidate interconnect technologies

#### Ultrasonically bonded wires

- Copper
- Aluminium
- Al clad Cu?
- Other metals Au?

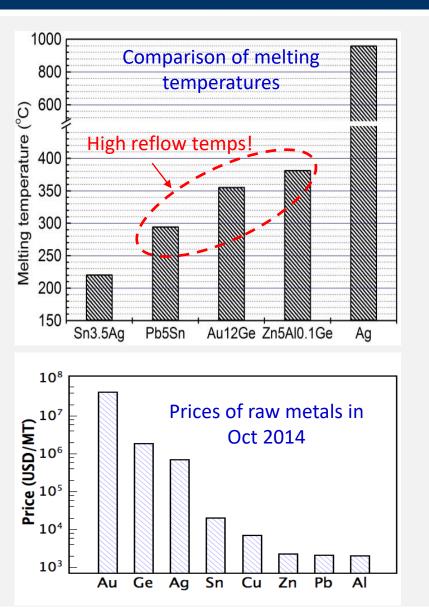
#### High temperature solders e.g. AuSn, AuGe, PbSn, ZnAl, ...

- Au-based alloys are expensive, high reflow temps
- Pb: environmental concerns and legislation

#### Alternatives to solder

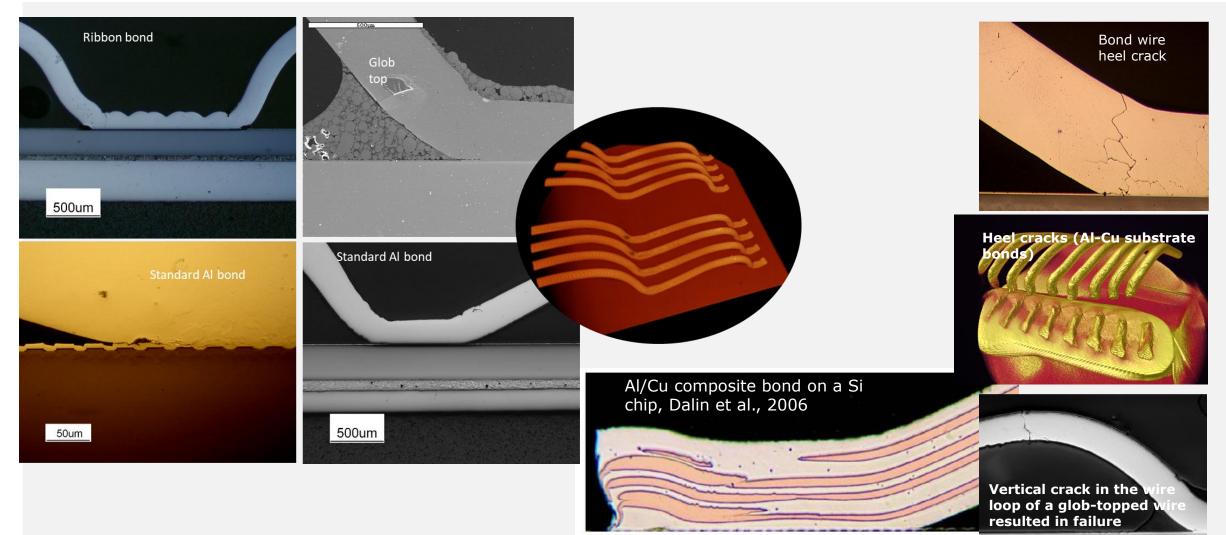
- Sintering of Ag particles or nanoparticles
- Emerging solder alloys
- Transient Liquid Phase soldering
- Liquid solder joints
- Local brazing
- Nanoparticle-enhanced solders
- Ultrasonic welding (e.g. for power terminals)





# Are Al wire and ribbon bonds suitable for high temp?



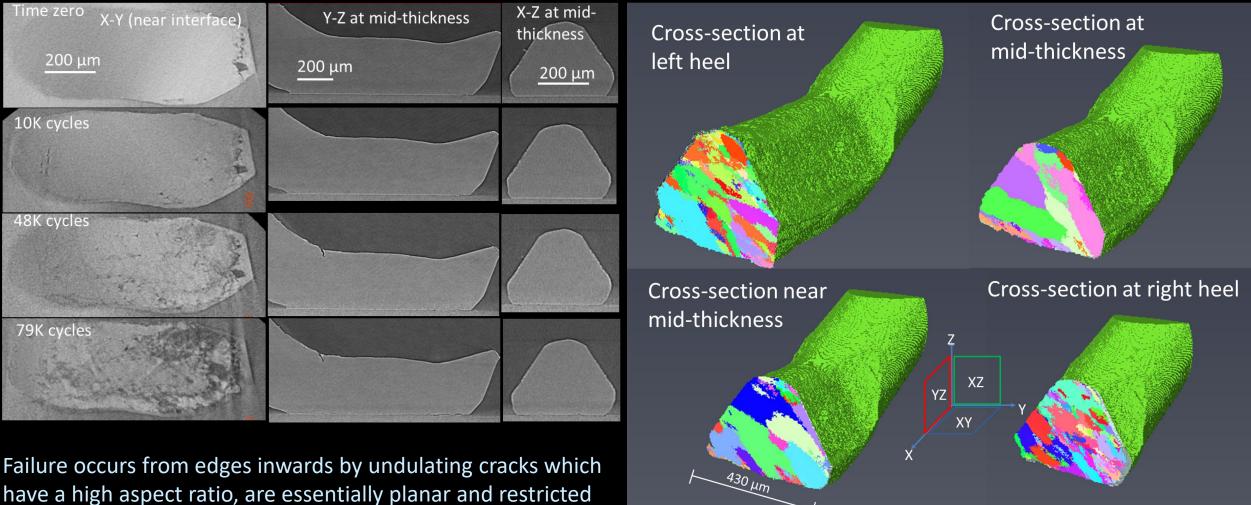




## Power cycling reliability in Al bond wires (40 - 120°C)

to interface region

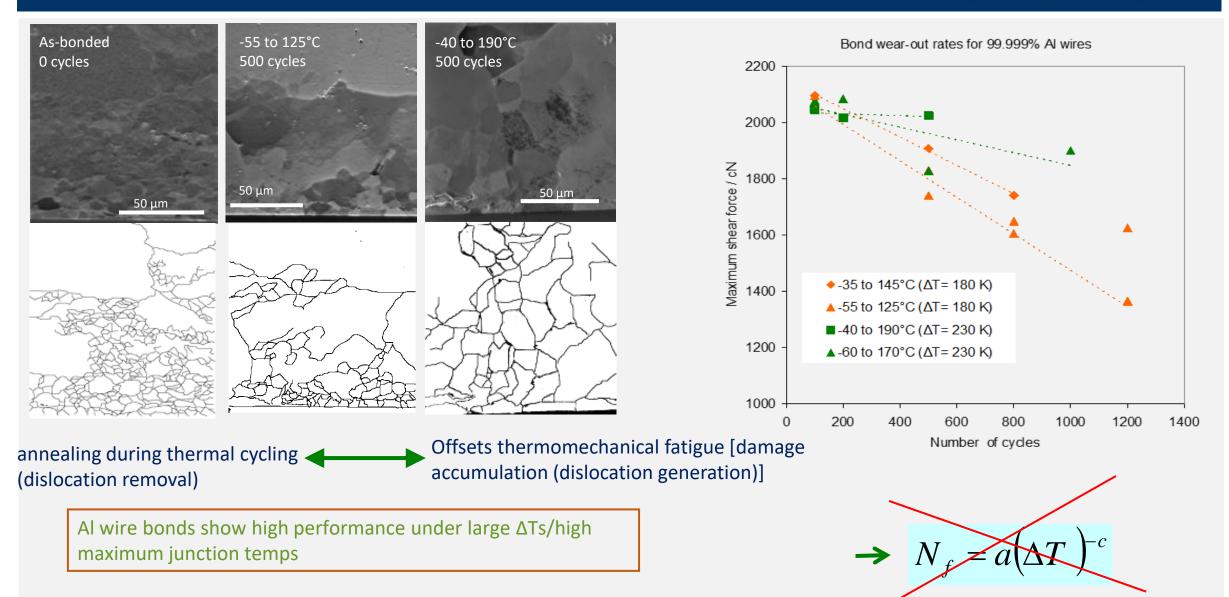
# Correlative Diffraction & absorption contrast tomography



- Wire flexing during loop formation
- Flexing also occurs during power cycling (heel regions experience compressive and tensile forces)
- Electromagnetic forces tend to push the bonds off the die laterally

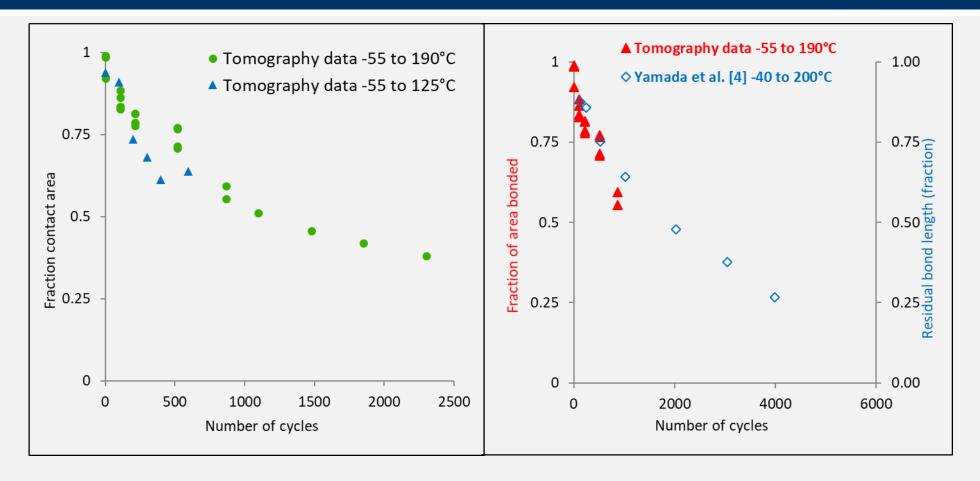
# Deviation from Coffin-Manson behaviour due to time-attemperature

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# Are Al wire and ribbon bonds suitable for high temp?





- Degradation rate quantified simply by measuring fraction of area bonded from X-ray CT 'same-sample' data
- Comparison with metallurgical cross-section data from Yamada *et al*. (2007) shows reasonable agreement

# **Copper Wire Bonding**

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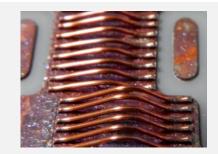
Copper is of increasing of interest as an alternative material to Al because

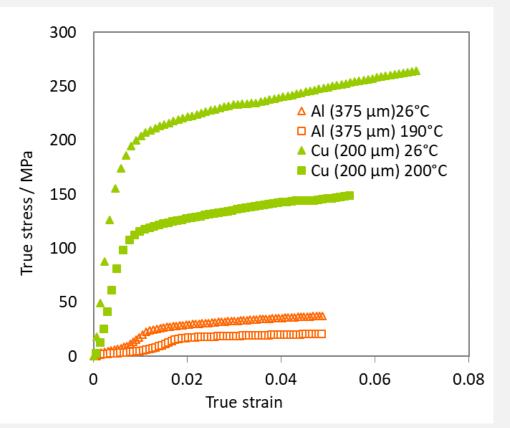
- Higher electrical and thermal conductivity that provide higher current densities
- Higher yield strength and mechanical stability which are expected to result in improved reliability

#### **Problem:**

Copper wire is much harder compared to aluminium and so requires higher bonding force and power which can potentially damage the bond pad area, this applies to both copper metalized die or DBC substrates

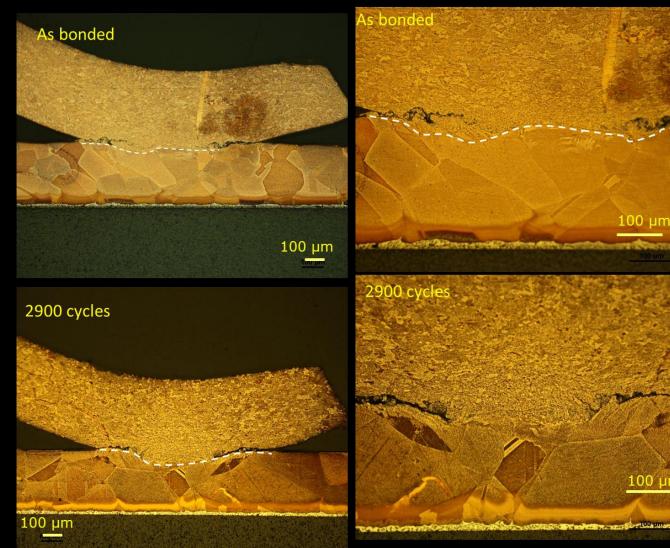
Material Properties	Aluminium	Copper
Thermal conductivity	220 W/m.K	400 W/m.K
CTE	25 ppm	16.5 ppm
Yield Strength	29 MPa	140 MPa
Melting point	660 0C	660 0C
Elastic modulus	50 GPa	110-140 GPa
Electrical resistivity	2.7 µOhm.cm	1.7 μOhm.cm





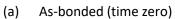
# Cu-Cu bond interface

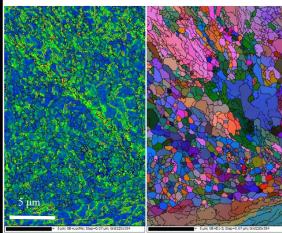
Microstructure of Cu-Cu (substrate) bond interface under passive cycling, -55 to 125°C



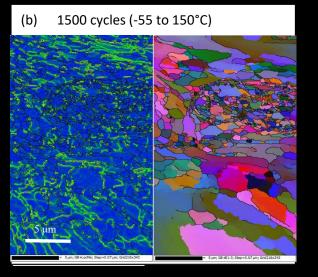
Little microstructural change & potential cyclic hardening

## Pre-annealed 380µm wires bonded on Orthodyne system (Dynex)-55 to 150°C



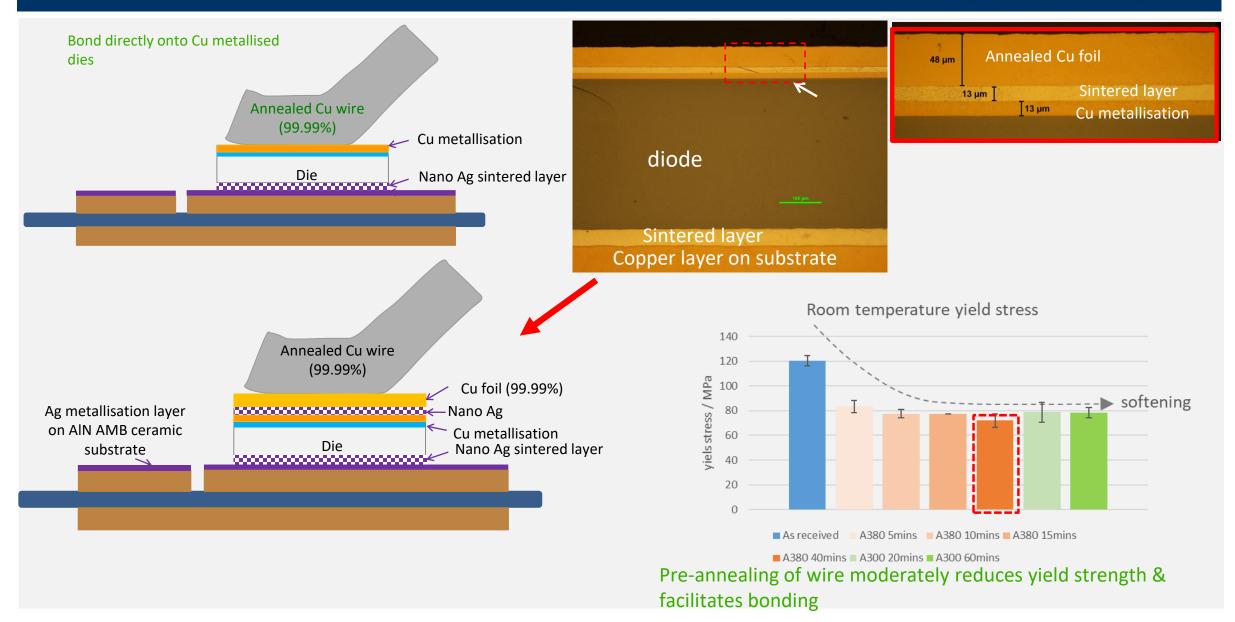


Continued recrystallisation under cycling & modest softening



# Ongoing research: bonding onto devices





# Al-clad Cu wires?



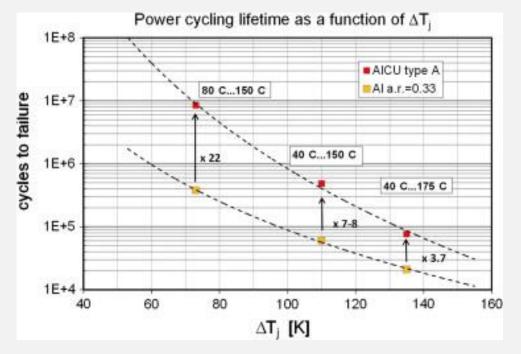
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#### Degradation mechanism? CTE issues?



Schmidt et al., Microelectronics Reliability Volume 52, Issues 9–10, Pages 2283-2288

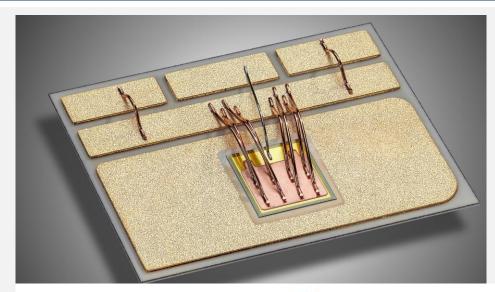


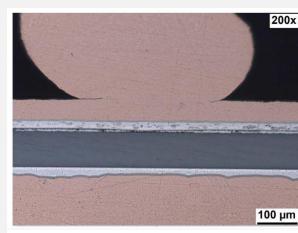
# Heraeus Die Top System

https://www.heraeus.com/media/media/het/doc\_het/products\_and\_solut ions\_het\_documents/material\_systems\_1/die\_top\_system\_docs/Flyer\_Die \_Top\_System-05-2018.pdf

# The University of **Nottingham**

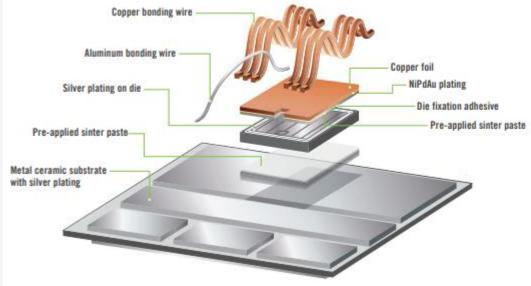
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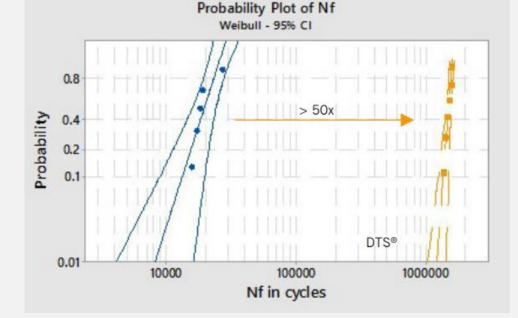




#### Die Top System®

- Silver-sintering Copper foil on top of each die
- Die protection against high bond forces during thick Copper wire bonding
- Spreads current flow
- Heat spreader  $\rightarrow$  lowers hot spot
- Significant increase of lifetime







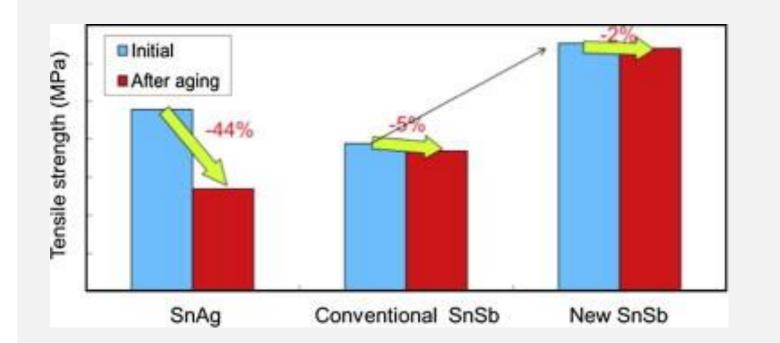
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# Solder alternatives & other interconnect

# Solid-solution strengthened solders have been proposed



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solidification thermodynamics- tight reflow temperature window

Tin-Antimony

Dietrich, Microelectronics Reliability 54 (2014) 1901–1905

No secondary precipitates, restricted deformation by solid-solution atoms, complex

# Sintered nano-silver attachments

- Higher thermal & electrical conductivity
- Single-phase material (no intermetallic compounds)
- Higher meting point, superior reliability
- Lower cost, less toxicity
- Modest sintering temperatures
- Processing challenges associated with ZnAl alloys and transient liquid phase soldering

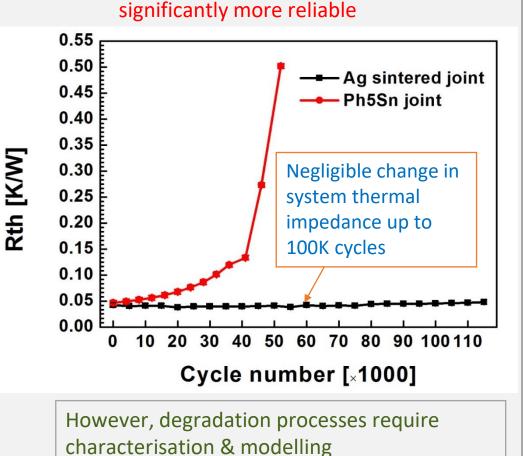
	SnAg (3.5)	Ag sintered
T <sub>m</sub> / °C	221	962
Thermal conductivity / W/M/K	70	240*
Electrical conductivity / MS/m	8	41
CTE / ppm/K	28	19
Tensile strength / MPa	30	55

Previous work show sintered attachments are

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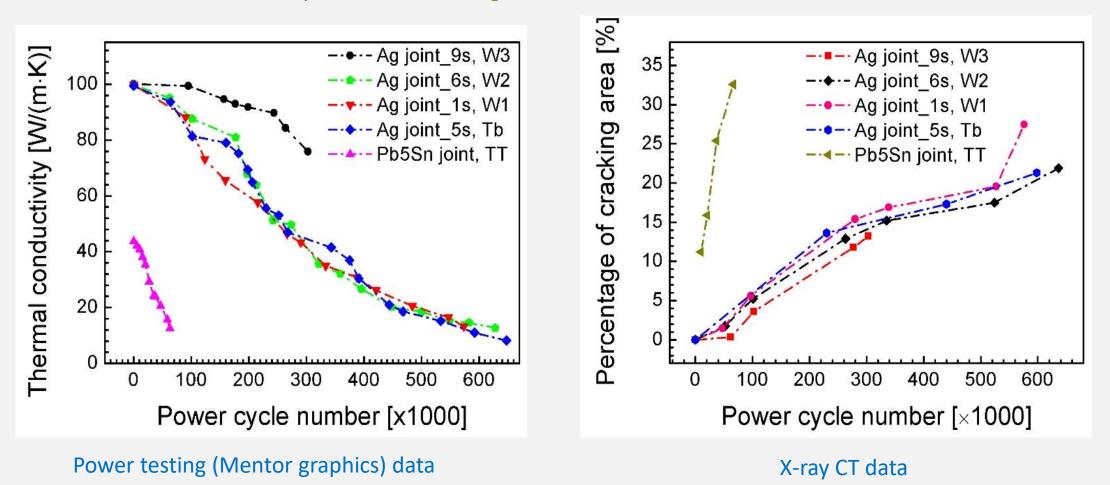
Dai, J et al., 2018.

\* Schueurmann *et al*.



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Non-destructive assessment of the **same specimen** using different techniques shows excellent correlation between thermal conductivity decrease & crack growth

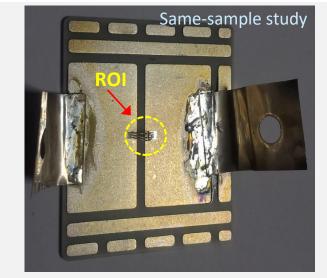


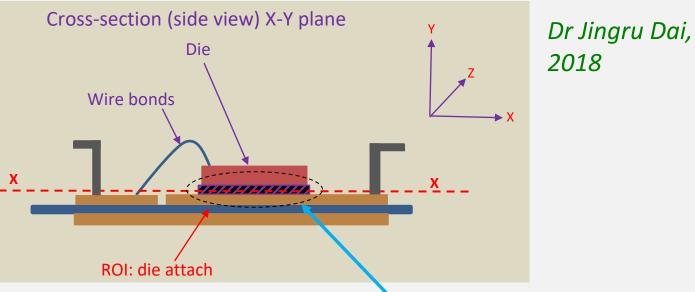
J. Dai, PhD Thesis 2018

# Reliability characterisation of sintered nanoAg die attach



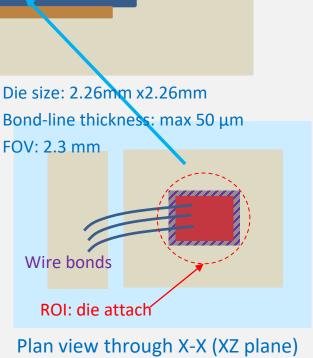
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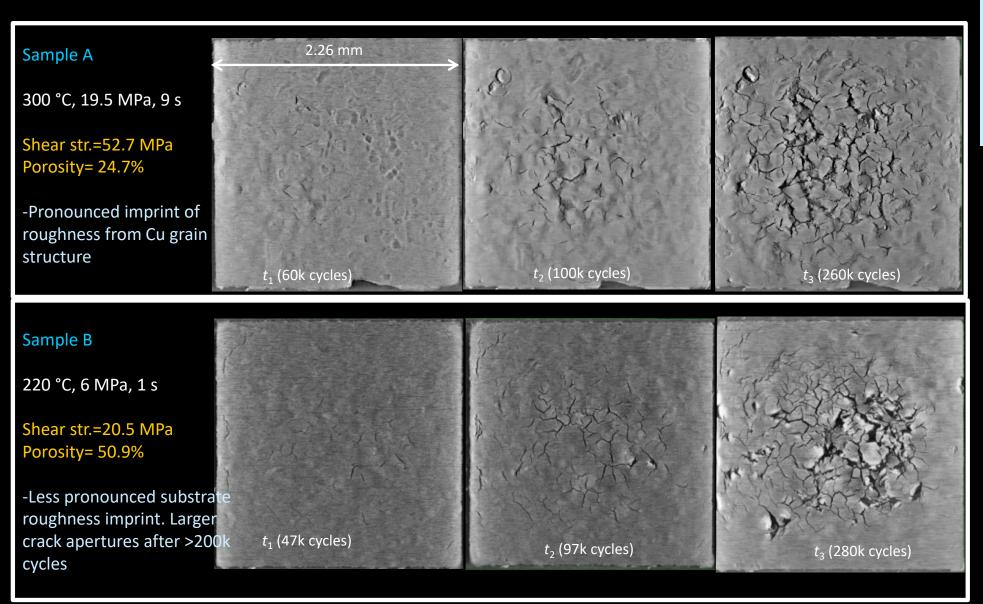


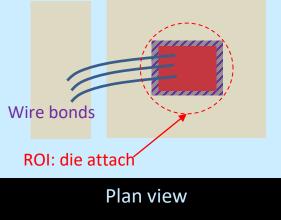
Materials:

- CREE CPW4-1200-S010B SiC power diodes with 1.4 mm thick Ni/Ag metallization on the cathode and ~4 mm thick AI metallization on the anode
- AIN- substrates (1 mm thick AIN ceramic tile sandwiched between 0.3 mm Cu tracks actively brazed on both sides, with 0.2 μm thick Ag finish)
- Nano Ag film (Argomax 2020): 62.3 μm thick, average particle size of ~20 nm
- Power cycling and thermal impedance characterisation on Mentor Graphics platform,
  ΔT= approx. 50 to 200 °C (150K)
- Correlation with non-destructive imaging using Zeiss Xradia Versa XRM500 3D X-ray microscope
- Image visualisation and analysis using Xradia 3D Viewer, Avizo Fire 9.01 & Dragonfly



# X-ray CT slices through same sample over time (lateral plane)

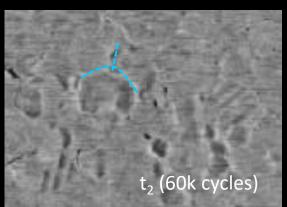




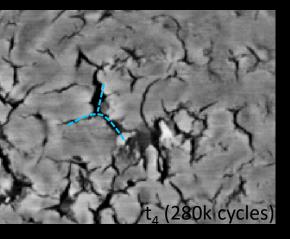
# Densification-driven shrinkage and crack formation high shear force, low porosity sample

XZ plane





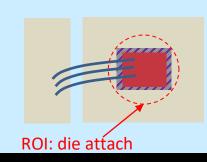
t<sub>2</sub> (100k cycles)



Note high pixel intensities adjacent to cracks

Texture of images (differing levels of x-ray absorption) is linked to non-uniform packing density due to depressions on the substrate

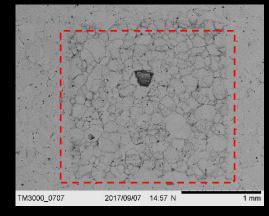
Cracks initiate in less dense areas, especially at points correlating to grain boundary triple points on substrate beneath Propagation occurs along grain boundaries



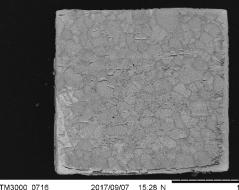
Plan view

## Shear/fracture surfaces

Substrate side (Cu)



Die side



Crack growth vs time, transfer across material boundary

## X-ray CT data: time series in X-Y plane

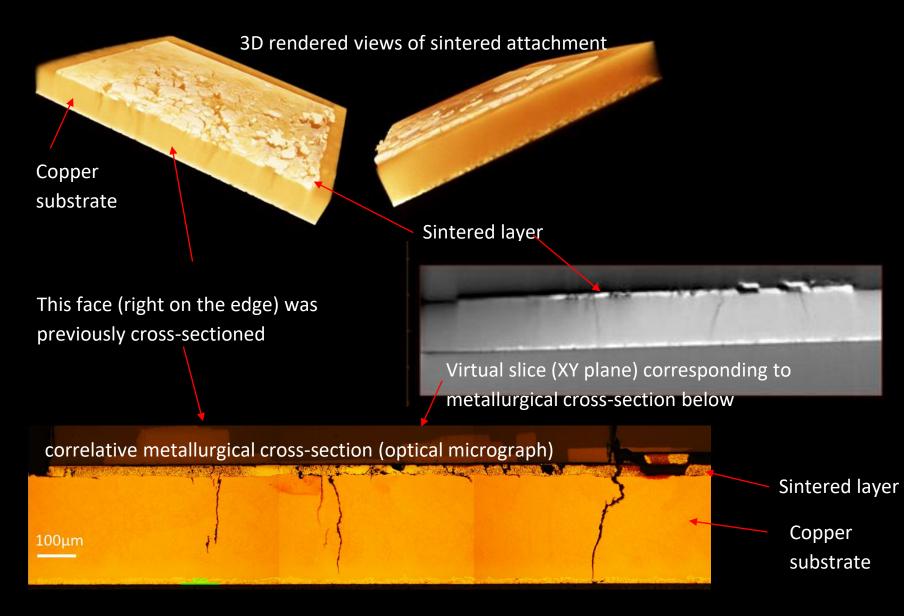


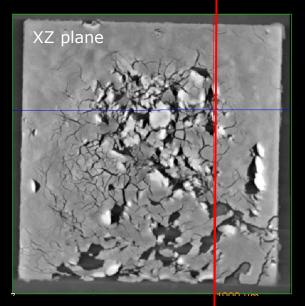
500 µm

highest pixel intensities right next to widest/most developed cracks

# Correlative microscopy

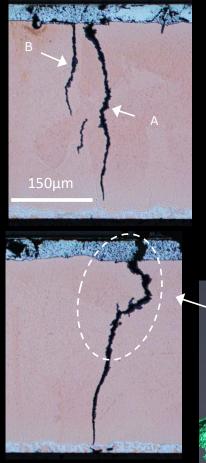
Sample B (low shear strength, high porosity) >600k thermomechanical fatigue cycles

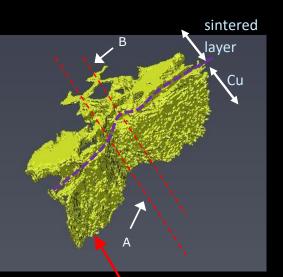




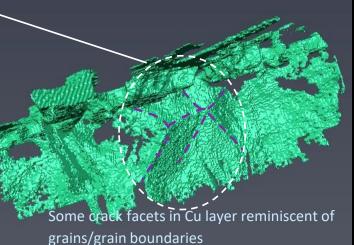
# Correlative visualisation of crack morphologies

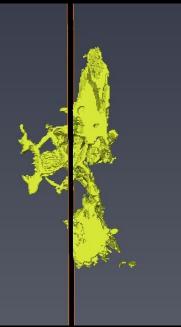
Crack facets/texture may be due to different orientation of cleavage planes in grains?



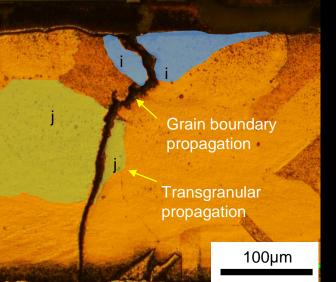


Crack tip in Cu substrate





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Further investigation of orientation relationship between the crack surfaces and crystallographic planes of grains: EBSD/DCT?

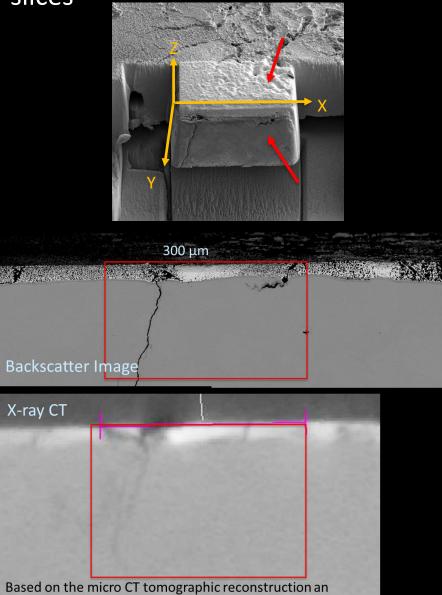
100µm

Intra-granular crack

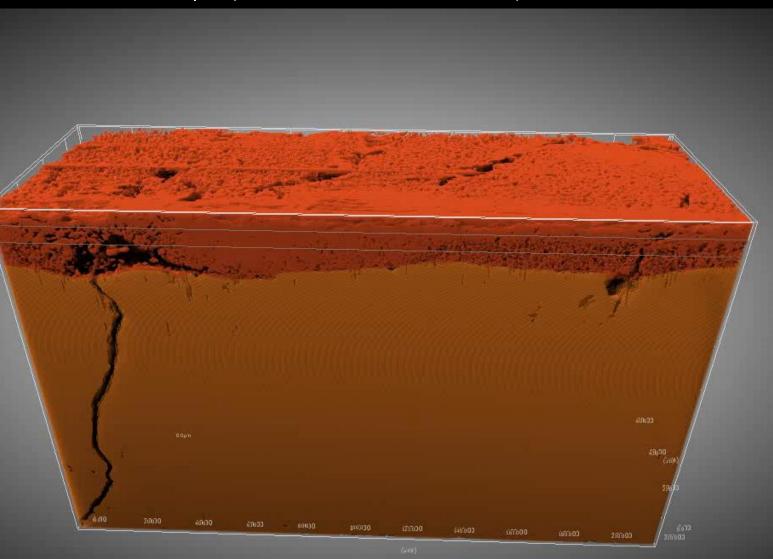
transfer points

Agyakwa et al., Journal of Microscopy, 277: 140-153 (2019). https://doi.org/10.1111/jmi.12803

# 3D reconstruction of serial FIB slices



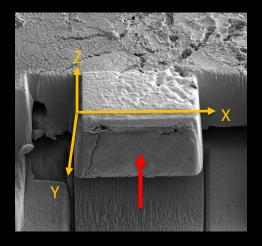
Based on the micro CT tomographic reconstruction an area was interest was selected and identified in the P-FIB A 3D sample was then prepared Voxel size X 260 μm @1536 pixel (169 nm / pixel) Y 173 μm @1024 pixel Z 100 μm (500 slices @200nm intervals)



Dr Stuart Robertson, LMCC Loughborough

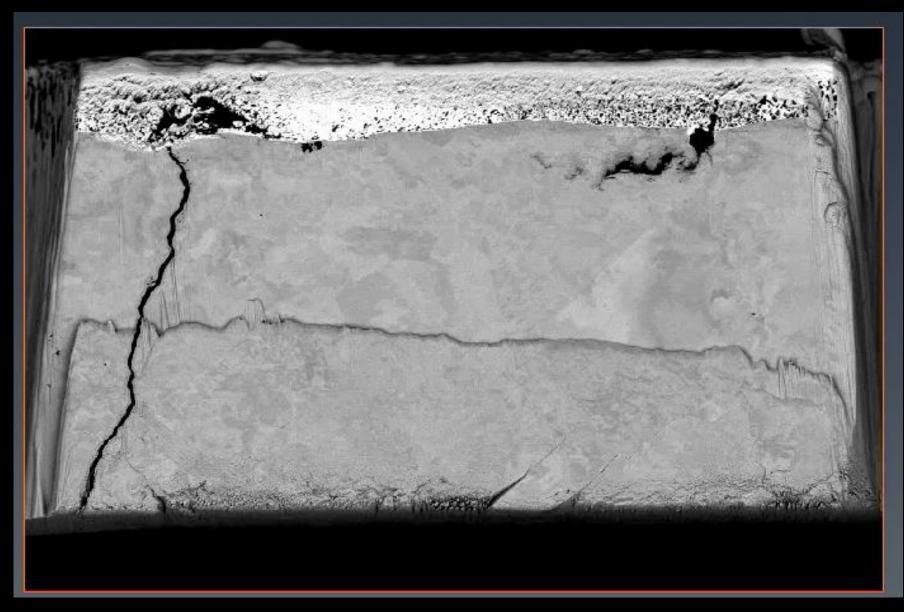
# Crack transfer across material boundaries (3D FIB)

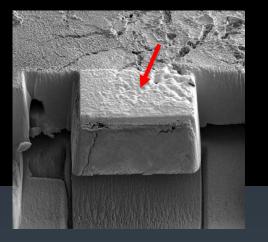
Courtesy of Dr Stuart Robertson, LMCC Loughborough



3D reconstruction of serial FIB slices

Through-thickness view

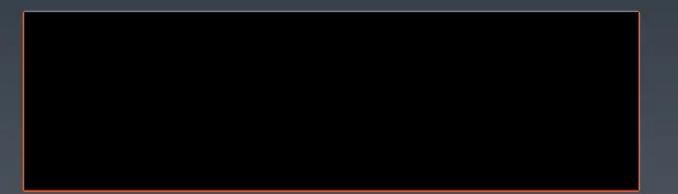




#### Lateral view

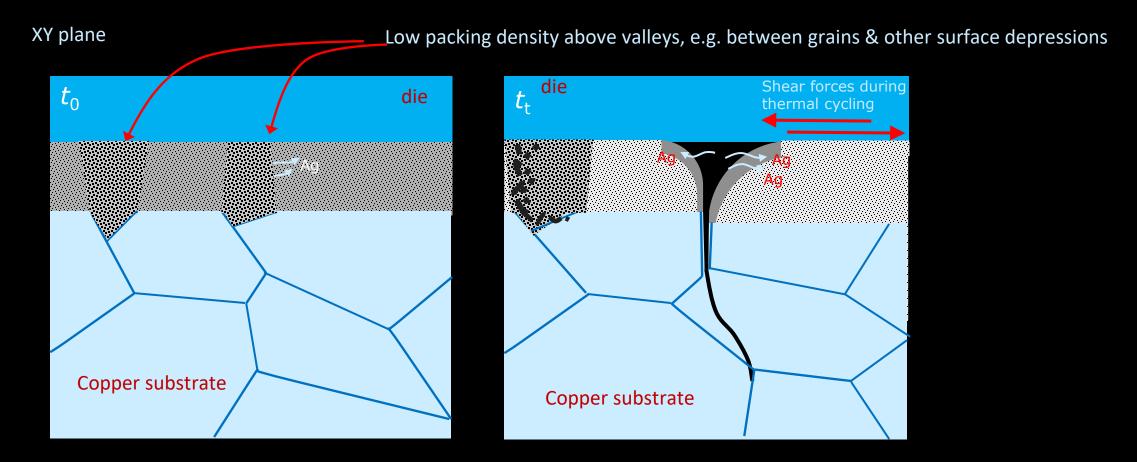
#### Dr Stuart Robertson, LMCC Loughborough

3D reconstruction of serial FIB slices



## Proposed densification & cracking model

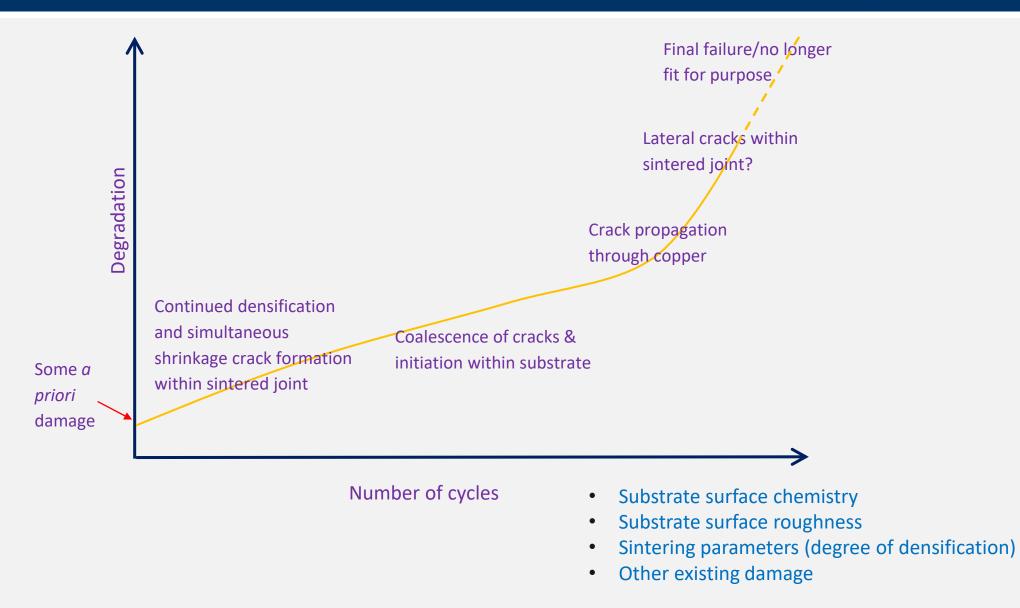
(1) Densification-driven shrinkage and crack formation within sintered joint



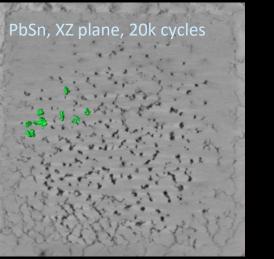
(2) Intergranular/transgranular propagation of crack through copper substrate

## Proposed damage model for sintered attachments

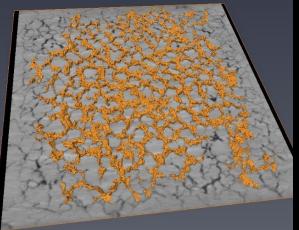




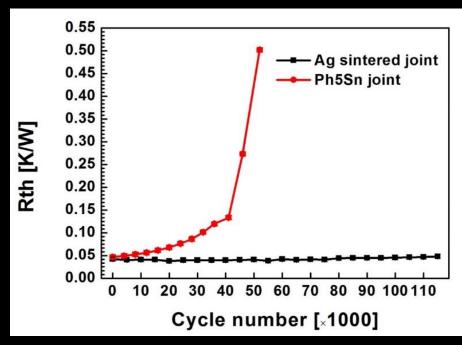
# Effect of damage morphology on reliability?



PbSn, XZ plane, 60k cycles



Comparing thermal performance under power cycling with PbSn solder joints



Damage accrues more rapidly in the PbSn solder under the same conditions

Could their morphological differences in damage may play a role? e.g. greater sphericity of PbSn damage

- lateral discontinuities have greater influence on the thermal path in the package

# Thank you



Dr Jingru Dai, Dr Bassem Mouawad, Dr Chris Parmenter, Dr Martin Corfield, Dr Li Yang, Dr Paul Evans, Dr Elaheh Arjmand, Dr Jianfeng Li, Dr Fang Xu, Prof Mark Johnson, Dr Imran Yacqub, Dr Yun Wang, Dr Rob Skuriat (University of Nottingham) Dr Stuart Robertson, Dr Zhaoxia Zhou (Loughborough University LMCC) Dr Lisa H. Chan, Dr Hrishikesh Bale, Dr Jun Sun (Carl Zeiss Microscopy & XNovo Tech) Prof Chris Bailey, Prof Hua Lu (University of Greenwich)

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